

isc N-Channel MOSFET Transistor

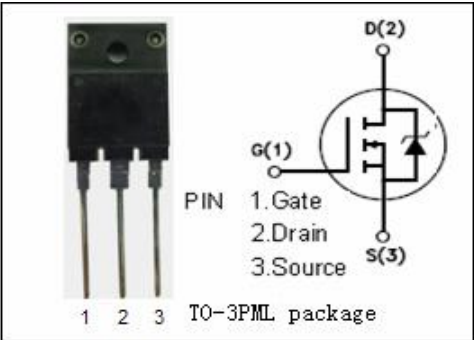
2SK1217

DESCRIPTION

- Drain Current $-I_D=8A@ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}=900V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- Designed for high voltage, high speed power switching

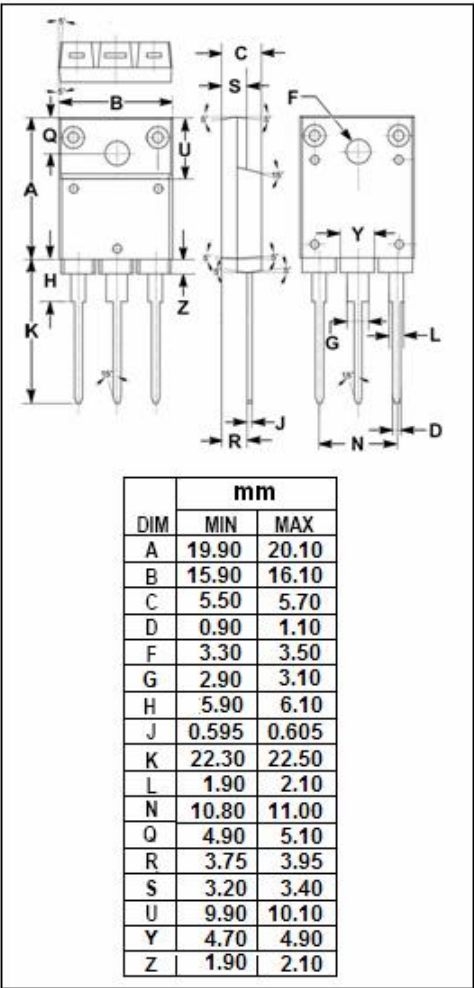


ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	8	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	100	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.25	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	30	$^{\circ}C/W$



isc N-Channel Mosfet Transistor**2SK1217****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	900			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	2.5	3.5	5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =4A		1.5	2.0	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =900V; V _{GS} = 0			500	uA
V _{SD}	Forward On-Voltage	I _S =8A; V _{GS} =0		1.0	1.5	V
tr	Rise time	V _{GS} =10V; I _D =8A; R _L =25 Ω		230	350	ns
ton	Turn-on time			280	425	ns
tf	Fall time			160	240	ns
toff	Turn-off time			620	690	ns